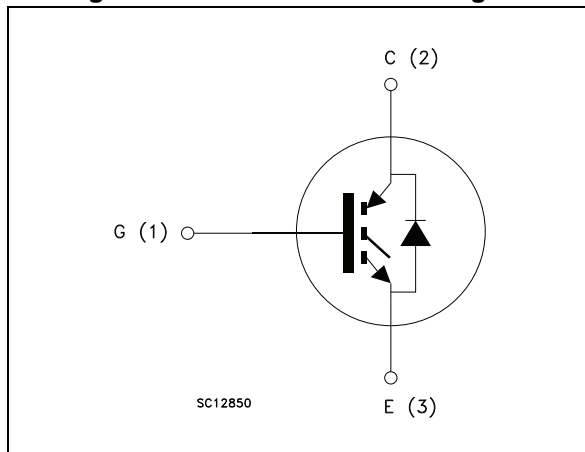


Figure 1. Internal schematic diagram



### Features

- Maximum junction temperature:  $T_J = 175\text{ °C}$
- High speed switching series
- Minimized tail current
- $V_{CE(sat)} = 2.1\text{ V (typ.) @ } I_C = 15\text{ A}$
- 5  $\mu\text{s}$  minimum short circuit withstand time at  $T_J = 150\text{ °C}$
- Safe paralleling
- Very fast recovery antiparallel diode
- Low thermal resistance

### Applications

- Uninterruptible power supply
- Welding machines
- Photovoltaic inverters
- Power factor correction
- High frequency converters

### Description

These devices are IGBTs developed using an advanced proprietary trench gate field-stop structure. These devices are part of the improved H series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of high frequency converters. Furthermore, a slightly positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1. Device summary

Order code	Marking	Package	Packaging
STGW15H120DF2	G15H120DF2	TO-247	Tube
STGWA15H120DF2	G15H120DF2	TO-247 long leads	Tube

# Contents

- 1      Electrical ratings ..... 3**
- 2      Electrical characteristics ..... 4**
  - 2.1    Electrical characteristics (curves) ..... 6
- 3      Test circuits ..... 11**
- 4      Package mechanical data ..... 12**
  - 4.1    TO-247, STGW15H120DF2 ..... 13
  - 4.2    TO-247 long leads, STGWA15H120DF2 ..... 15
- 5      Revision history ..... 17**

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )	1200	V
$I_C$	Continuous collector current at $T_C = 25\text{ °C}$	30	A
	Continuous collector current at $T_C = 100\text{ °C}$	15	A
$I_{CP}^{(1)}$	Pulsed collector current	60	A
$V_{GE}$	Gate-emitter voltage	$\pm 20$	V
$I_F$	Continuous collector current at $T_C = 25\text{ °C}$	30	A
	Continuous collector current at $T_C = 100\text{ °C}$	15	A
$I_{FP}^{(1)}$	Pulsed forward current	60	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	259	W
$T_{STG}$	Storage temperature range	-55 to 150	°C
$T_J$	Operating junction temperature	-55 to 175	°C

1. Pulse width limited by maximum junction temperature.

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case IGBT	0.58	°C/W
$R_{thJC}$	Thermal resistance junction-case diode	1.47	°C/W
$R_{thJA}$	Thermal resistance junction-ambient	50	°C/W

## 2 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified.

**Table 4. Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ( $V_{GE} = 0$ )	$I_C = 2\text{ mA}$	1200			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 15\text{ A}$		2.1	2.6	V
		$V_{GE} = 15\text{ V}, I_C = 15\text{ A}$ $T_J = 125\text{ °C}$		2.4		
		$V_{GE} = 15\text{ V}, I_C = 15\text{ A}$ $T_J = 175\text{ °C}$		2.5		
$V_F$	Forward on-voltage	$I_F = 15\text{ A}$		3.5	4.4	V
		$I_F = 15\text{ A}, T_J = 125\text{ °C}$		2.6		
		$I_F = 15\text{ A}, T_J = 175\text{ °C}$		2.2		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 500\text{ }\mu\text{A}$	5	6	7	V
$I_{CES}$	Collector cut-off current ( $V_{GE} = 0$ )	$V_{CE} = 1200\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current ( $V_{CE} = 0$ )	$V_{GE} = \pm 20\text{ V}$			250	nA

**Table 5. Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GE} = 0$	-	1300	-	pF
$C_{oes}$	Output capacitance		-	105	-	pF
$C_{res}$	Reverse transfer capacitance		-	32	-	pF
$Q_g$	Total gate charge	$V_{CC} = 960\text{ V}, I_C = 15\text{ A},$ $V_{GE} = 15\text{ V},$ see <a href="#">Figure 29</a>	-	67	-	nC
$Q_{ge}$	Gate-emitter charge		-	8	-	nC
$Q_{gc}$	Gate-collector charge		-	38	-	nC

Table 6. IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 600\text{ V}$ , $I_C = 15\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , see <a href="#">Figure 28</a>	-	23	-	ns
$t_r$	Current rise time		-	7.4	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1621	-	A/ $\mu\text{s}$
$t_{d(off)}$	Turn-off delay time		-	111	-	ns
$t_f$	Current fall time		-	111	-	ns
$E_{on}^{(1)}$	Turn-on switching losses		-	0.38	-	mJ
$E_{off}^{(2)}$	Turn-off switching losses		-	0.37	-	mJ
$E_{ts}$	Total switching losses	-	0.75	-	mJ	
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 600\text{ V}$ , $I_C = 15\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$ , see <a href="#">Figure 28</a>	-	23.5	-	ns
$t_r$	Current rise time		-	8	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1525	-	A/ $\mu\text{s}$
$t_{d(off)}$	Turn-off delay time		-	118	-	ns
$t_f$	Current fall time		-	253	-	ns
$E_{on}^{(1)}$	Turn-on switching losses		-	0.65	-	mJ
$E_{off}^{(2)}$	Turn-off switching losses		-	0.93	-	mJ
$E_{ts}$	Total switching losses	-	1.58	-	mJ	
$t_{sc}$	Short-circuit withstand time	$V_{CE} = 600\text{ V}$ , $V_{GE} = 15\text{ V}$ , $T_J = 150\text{ }^\circ\text{C}$ ,	5		-	$\mu\text{s}$

1. Energy losses include reverse recovery of the external diode.
2. Turn-off losses include also the tail of the collector current.

Table 7. Diode switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$I_F = 15\text{ A}$ , $V_R = 600\text{ V}$ , $di/dt=1000\text{ A}/\mu\text{s}$ , $V_{GE} = 15\text{ V}$ , see <a href="#">Figure 28</a>	-	231	-	ns
$Q_{rr}$	Reverse recovery charge		-	0.72	-	$\mu\text{C}$
$I_{rrm}$	Reverse recovery current		-	14.5	-	A
$dl_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$		-	1200	-	A/ $\mu\text{s}$
$E_{rr}$	Reverse recovery energy		-	0.4	-	mJ
$t_{rr}$	Reverse recovery time	$I_F = 15\text{ A}$ , $V_R = 600\text{ V}$ , $di/dt=1000\text{ A}/\mu\text{s}$ , $V_{GE} = 15\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$ , see <a href="#">Figure 28</a>	-	414	-	ns
$Q_{rr}$	Reverse recovery charge		-	2.2	-	$\mu\text{C}$
$I_{rrm}$	Reverse recovery current		-	21.5	-	A
$dl_{rr}/dt$	Peak rate of fall of reverse recovery current during $t_b$		-	632	-	A/ $\mu\text{s}$
$E_{rr}$	Reverse recovery energy		-	1.3	-	mJ

## 2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature

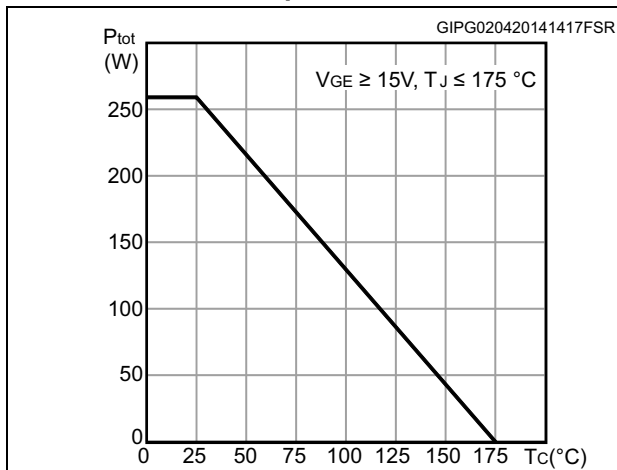


Figure 3. Collector current vs. case temperature

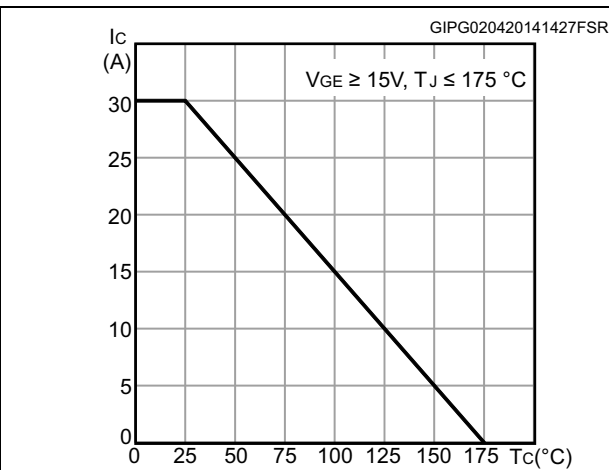


Figure 4. Output characteristics (T<sub>J</sub> = 25°C)

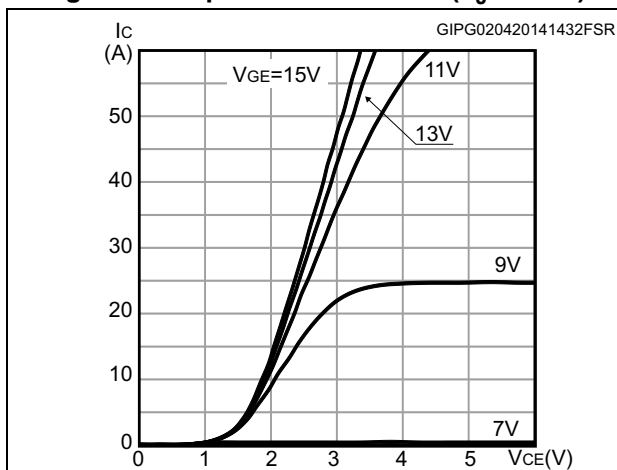


Figure 5. Output characteristics (T<sub>J</sub> = 175°C)

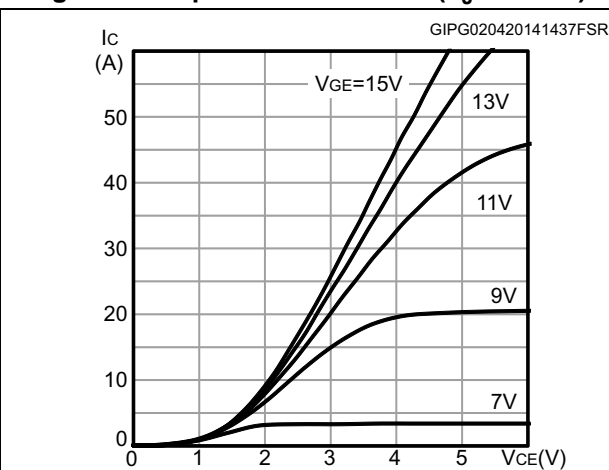


Figure 6. V<sub>CE(sat)</sub> vs. junction temperature

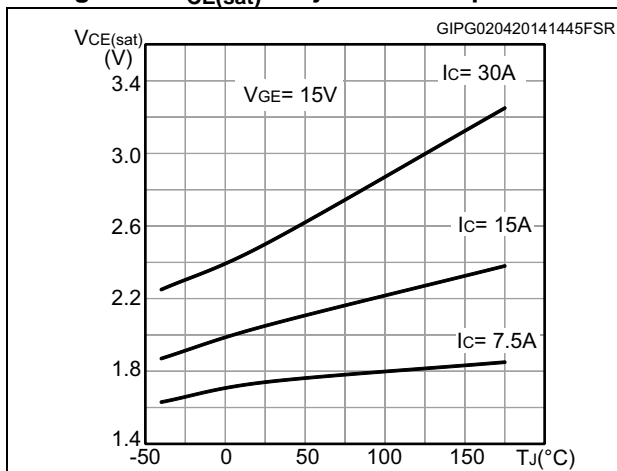


Figure 7. V<sub>CE(sat)</sub> vs. collector current

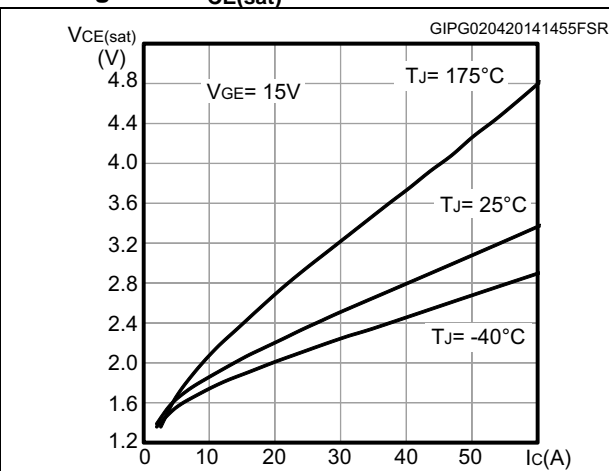


Figure 8. Collector current vs. switching frequency

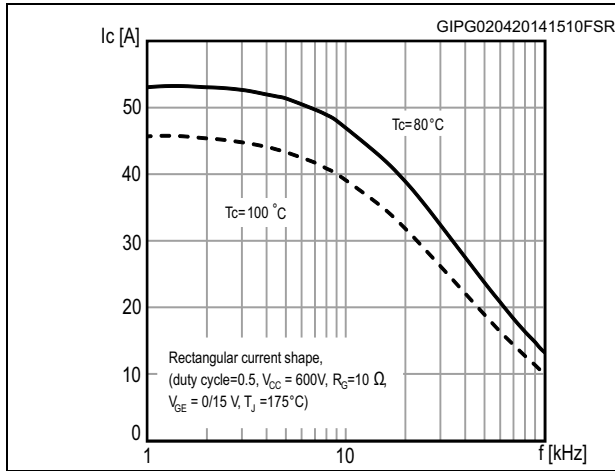


Figure 9. Forward bias safe operating area

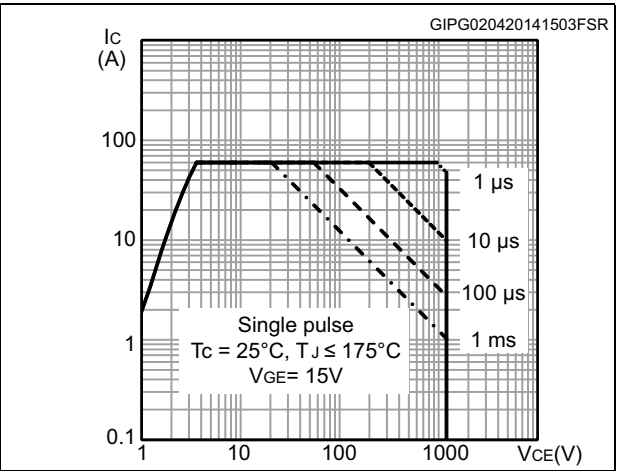


Figure 10. Transfer characteristics

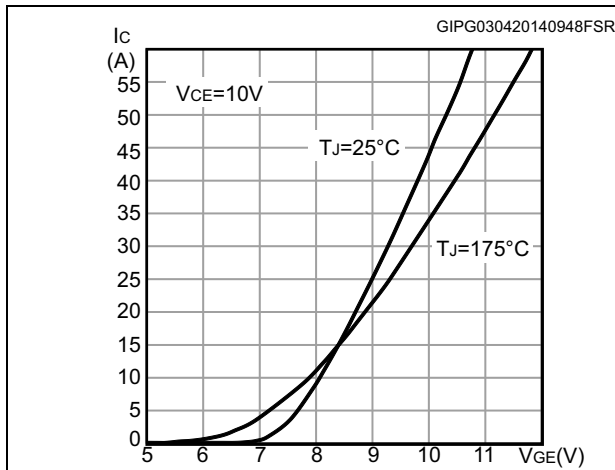


Figure 11. Normalized VGE(th) vs junction temperature

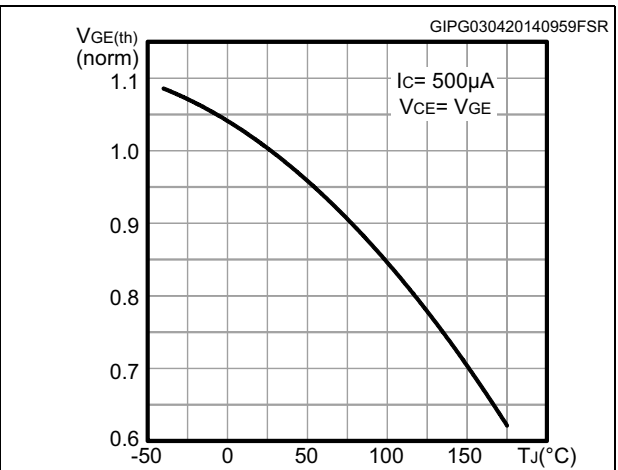


Figure 12. Normalized V(BR)CES vs. junction temperature

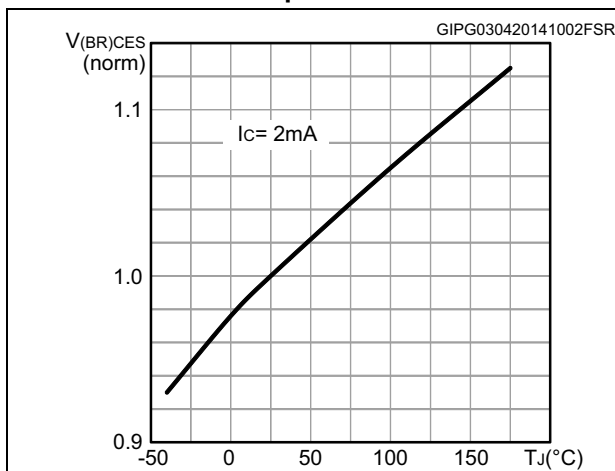


Figure 13. Capacitance variation

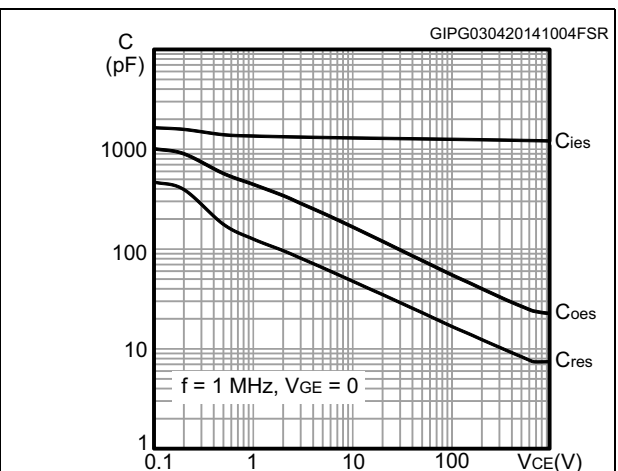


Figure 14. Gate charge vs. gate-emitter voltage

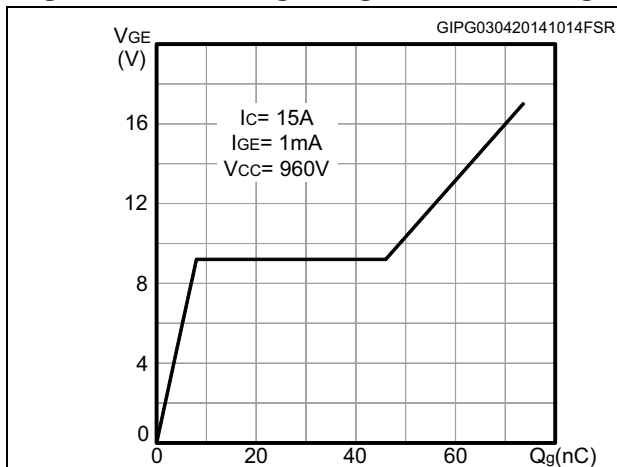


Figure 15. Switching loss vs collector current

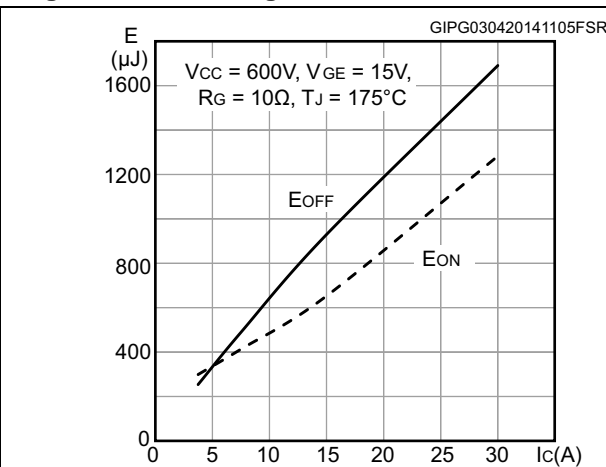


Figure 16. Switching loss vs gate resistance

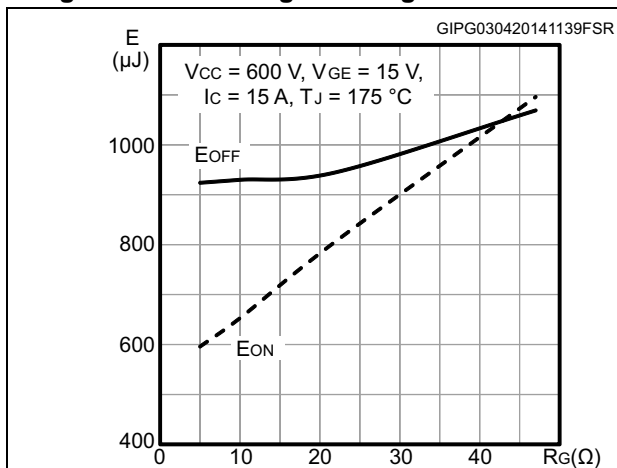


Figure 17. Switching loss vs temperature

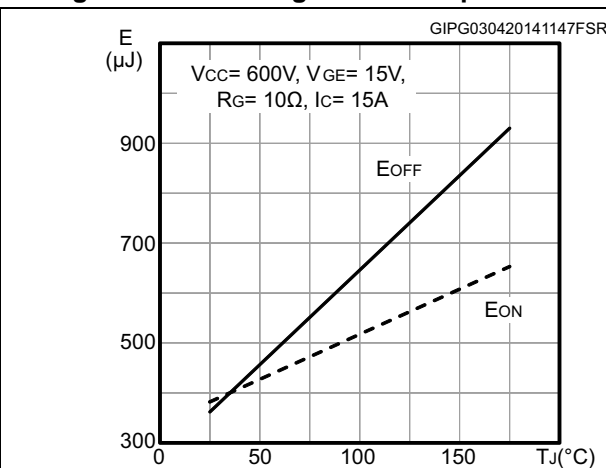


Figure 18. Switching loss vs collector-emitter voltage

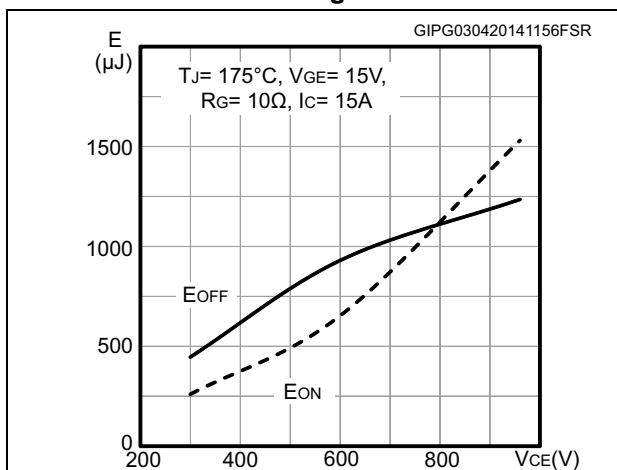


Figure 19. Switching times vs. gate resistance

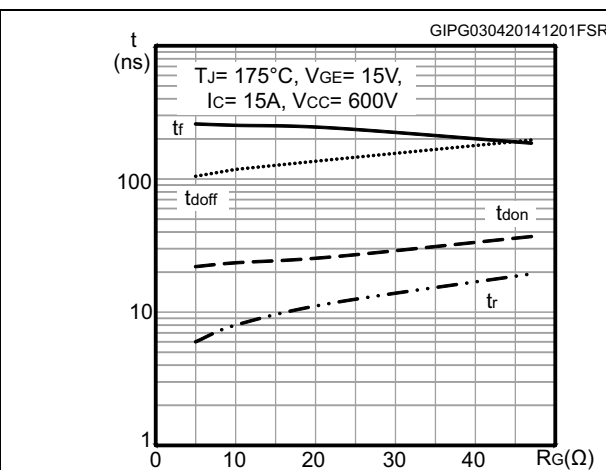




Figure 20. Switching times vs. collector current

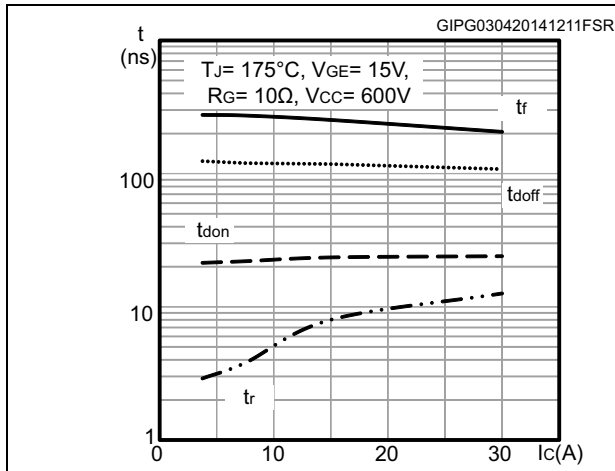


Figure 21. Diode  $V_F$  vs. forward current

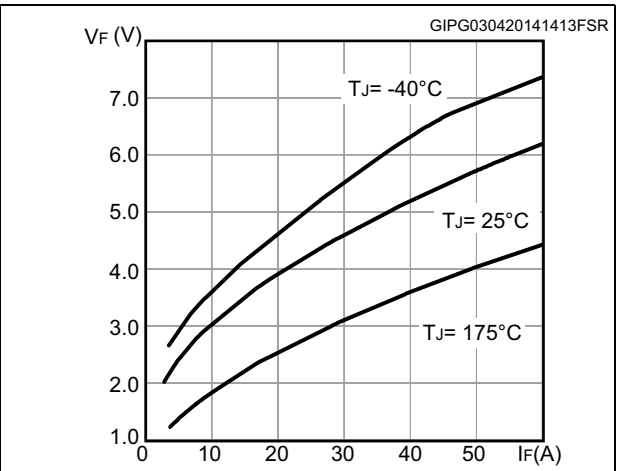


Figure 22. Reverse recovery current vs. diode current slope

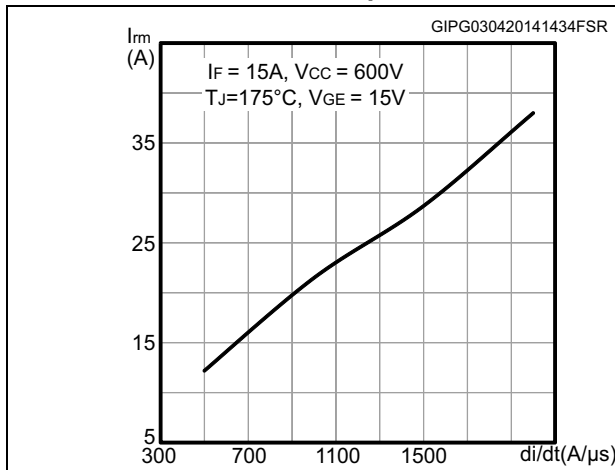


Figure 23. Reverse recovery time vs. diode current slope

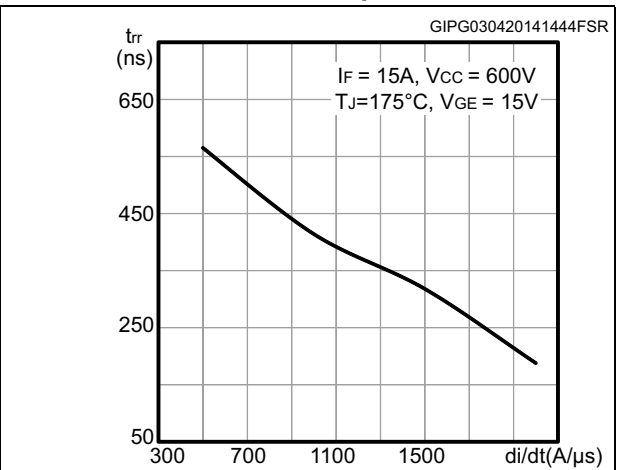


Figure 24. Reverse recovery charge vs. diode current slope

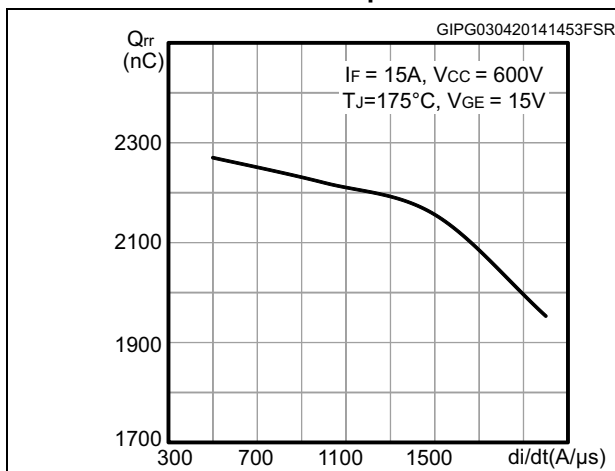


Figure 25. Reverse recovery energy vs. diode current slope

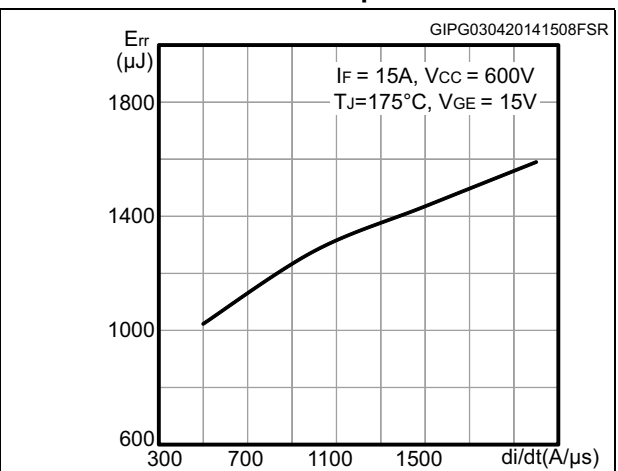


Figure 26. Thermal impedance for IGBT

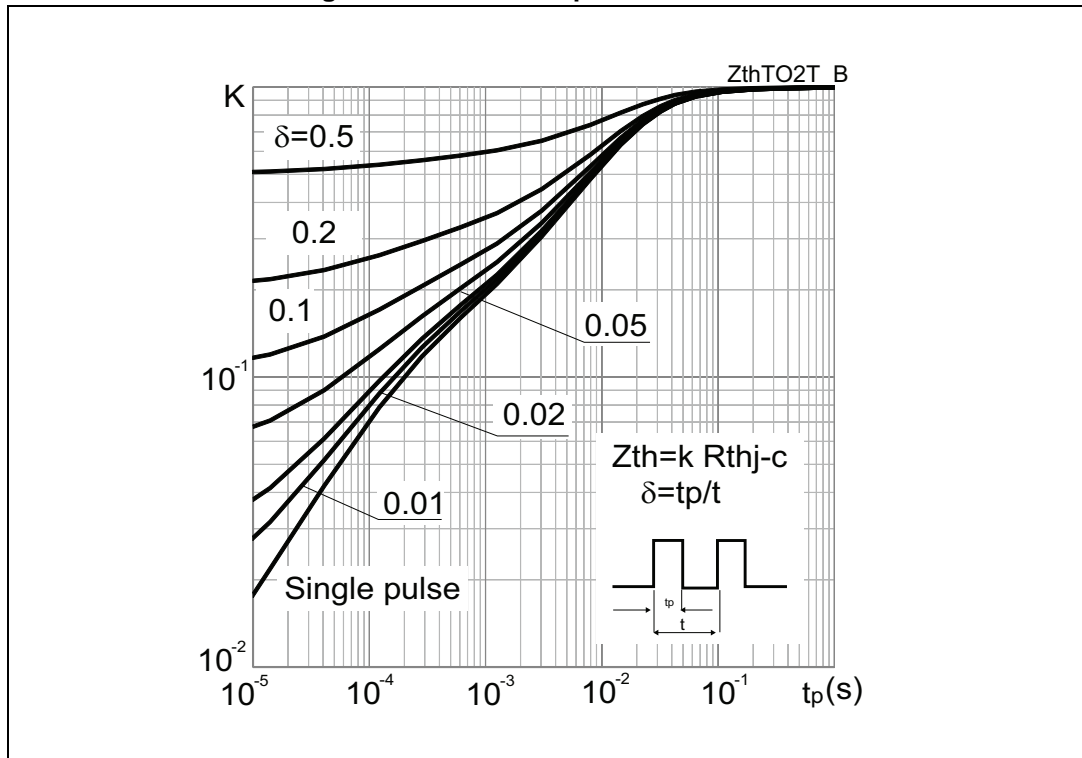
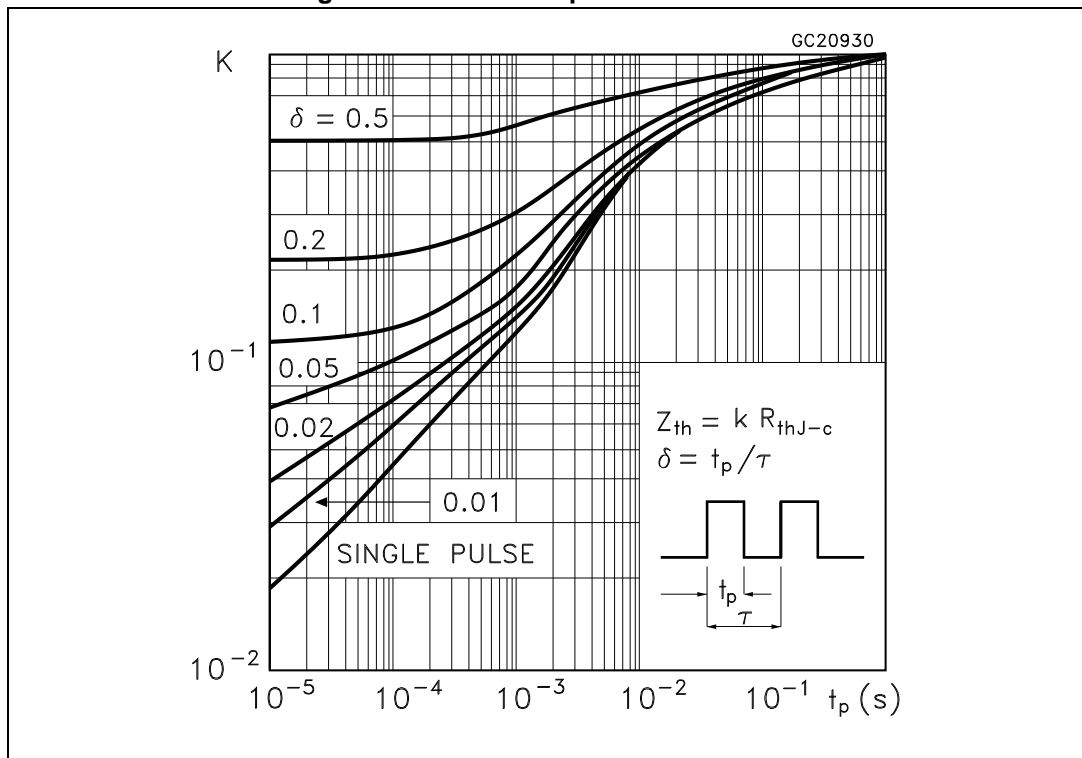


Figure 27. Thermal impedance for diode



### 3 Test circuits

Figure 28. Test circuit for inductive load switching

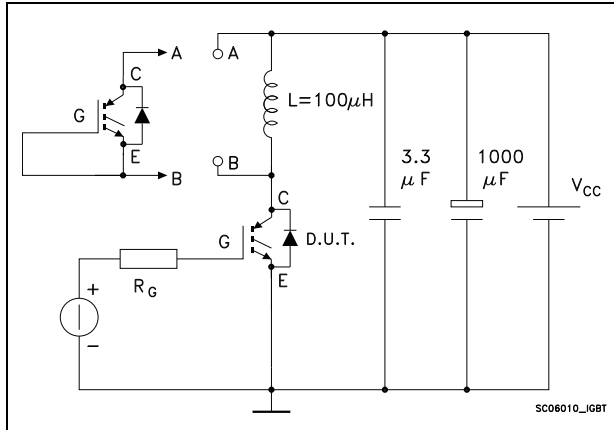


Figure 29. Gate charge test circuit

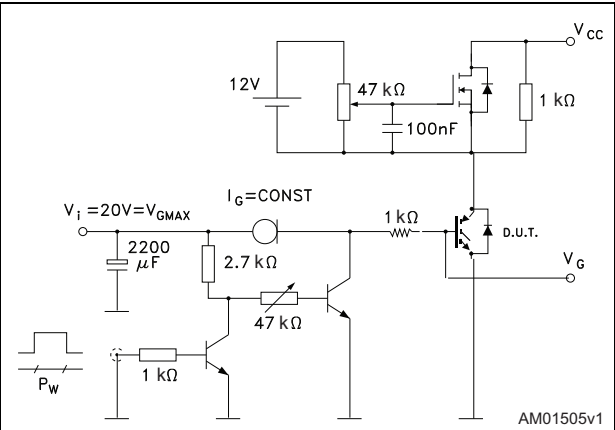


Figure 30. Switching waveform

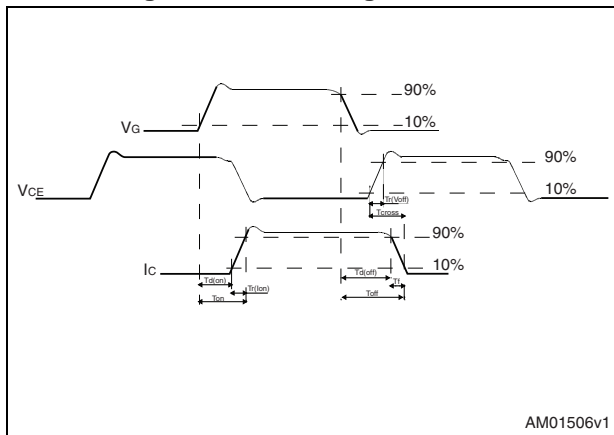
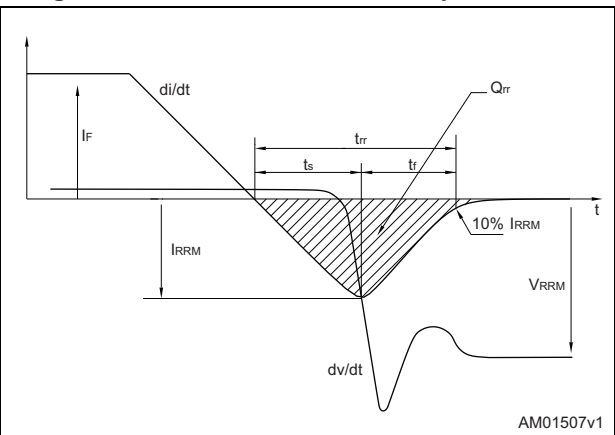


Figure 31. Diode reverse recovery waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-247, STGW15H120DF2

Figure 32. TO-247 drawing

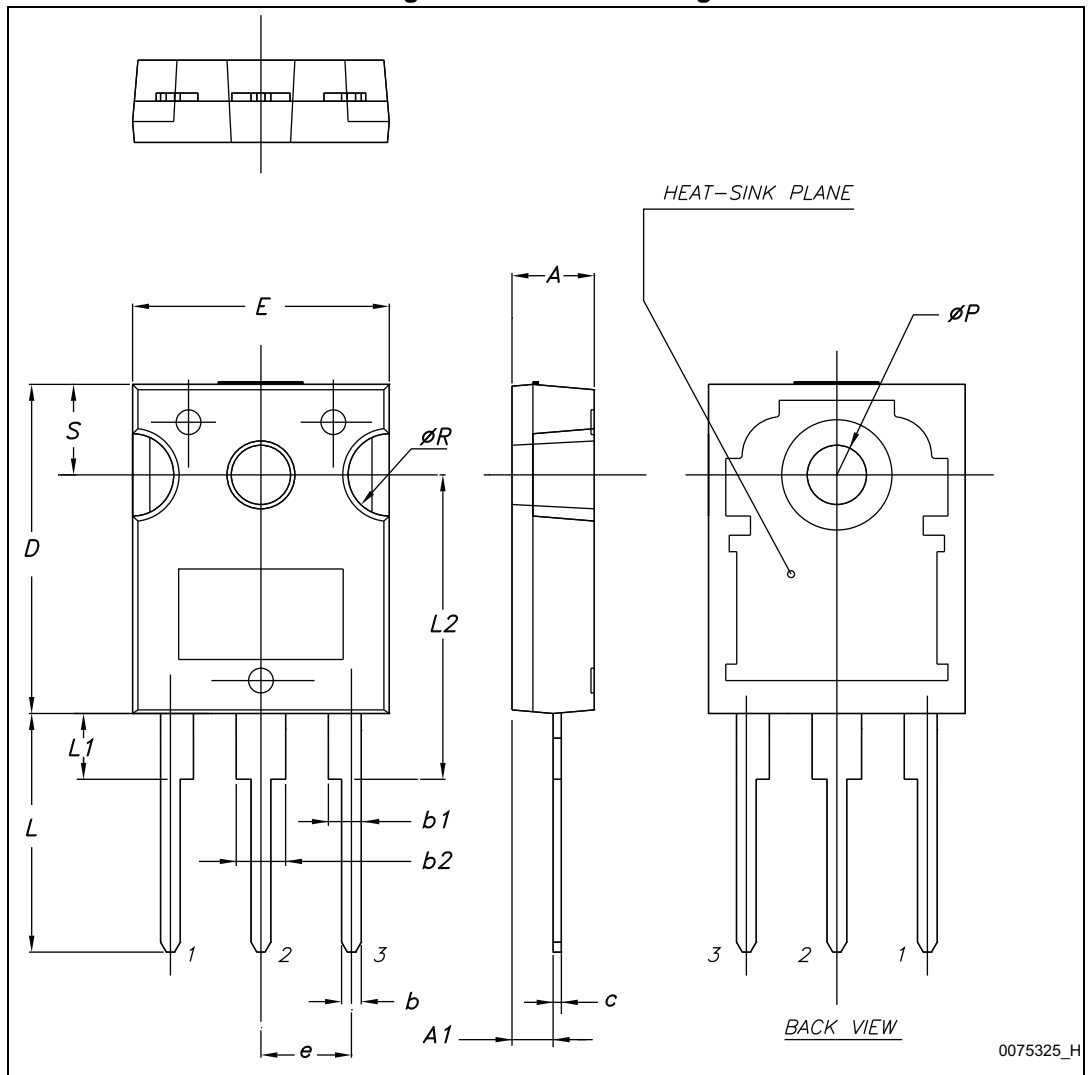


Table 8. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

### 4.2 TO-247 long leads, STGWA15H120DF2

Figure 33. TO-247 long leads drawing

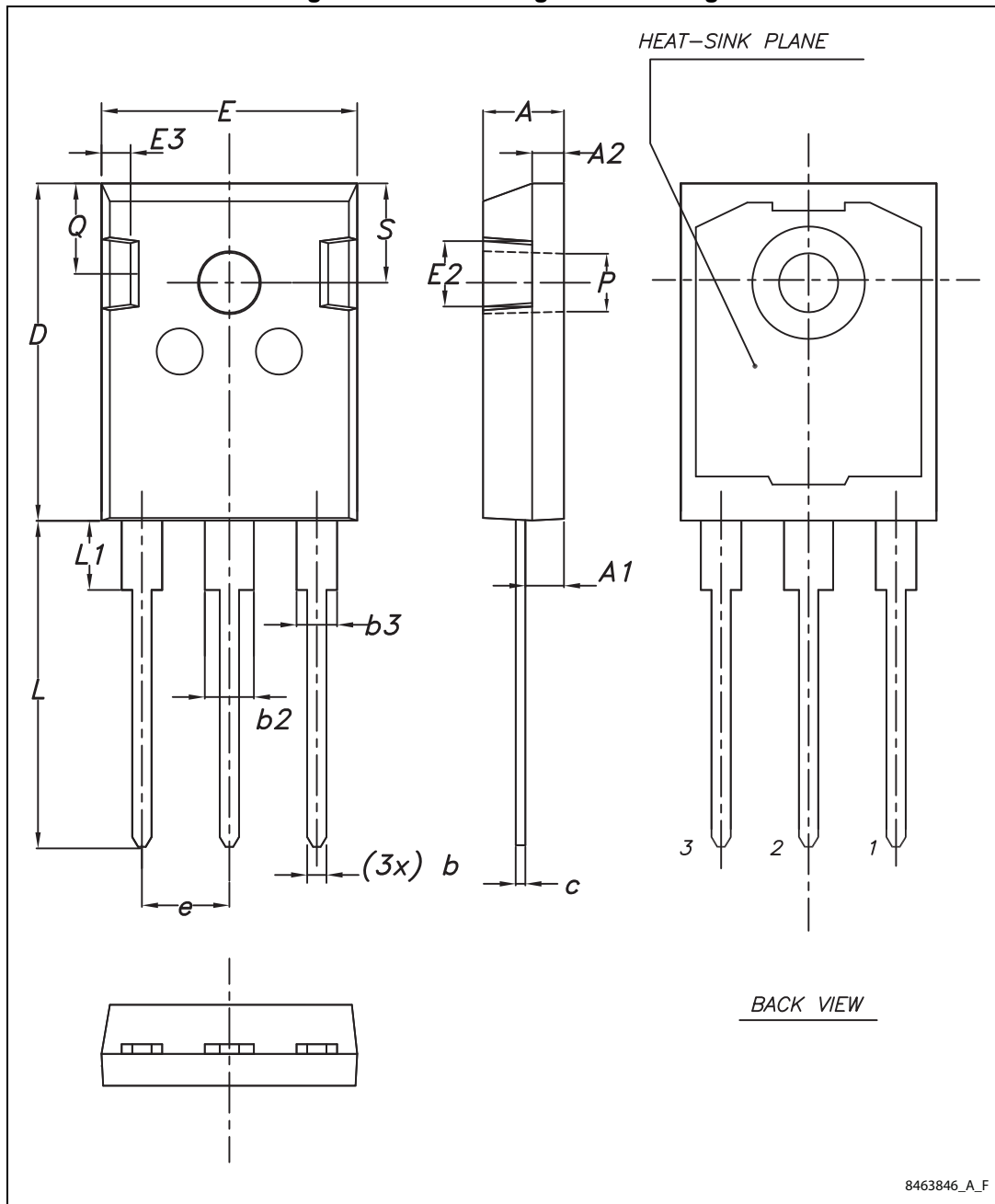


Table 9. TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25



## 5 Revision history

**Table 10. Document revision history**

Date	Revision	Changes
03-Oct-2012	1	Initial release.
03-Mar-2014	2	Updated title and features in cover page. Updated <a href="#">Section 4: Package mechanical data</a> . Minor text changes.
08-Apr-2014	3	Added <a href="#">Section 2.1: Electrical characteristics (curves)</a> . Minor text changes.
29-Jan-2015	4	Added <a href="#">4.2: TO-247 long leads, STGWA15H120DF2</a> . Updated <a href="#">Figure 29.: Gate charge test circuit</a> . Updated <a href="#">Figure 30.: Switching waveform</a> and <a href="#">Figure 31.: Diode reverse recovery waveform</a> . Minor text changes.
04-Mar-2015	5	Updated <a href="#">Figure 5.: Output characteristics (<math>T_J = 175^\circ\text{C}</math>)</a> . Minor text changes.

**IMPORTANT NOTICE – PLEASE READ CAREFULLY**

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2015 STMicroelectronics – All rights reserved



## Стандарт Электрон Связь

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331